

## CESD5V0D5 ESD Protection Diodes

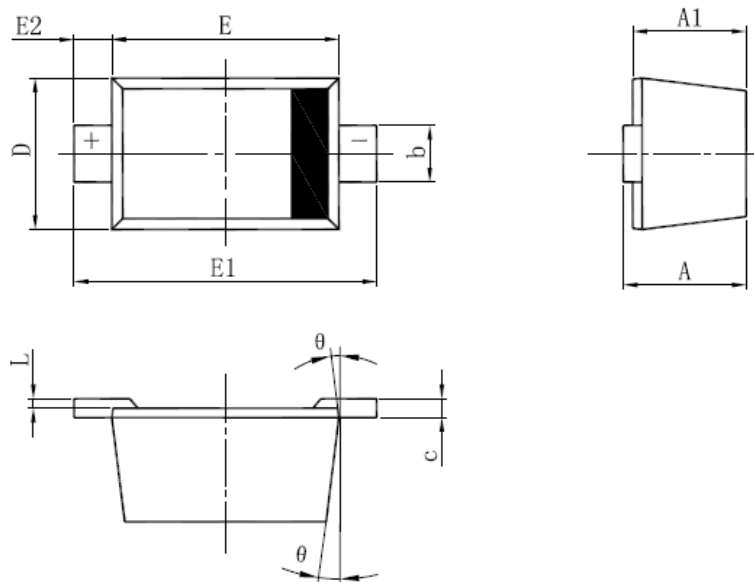
### Description:

The CESD5V0D5 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

### Mechanical Data:

- Stand-off Voltage: 3.3 V–12 V
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000–4–2 Level 4 ESD Protection
- These are Pb-Free Devices

### Mechanical Dimensions: In Inches/mm



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.510	0.770	0.020	0.031
A1	0.500	0.700	0.020	0.028
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	0.750	0.850	0.030	0.033
E	1.100	1.300	0.043	0.051
E1	1.500	1.700	0.059	0.067
E2	0.200 REF		0.008 REF	
L	0.010	0.070	0.001	0.003
θ	7° REF		7° REF	

### SOD-523

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- <http://www.smc-diodes.com> - [sales@smc-diodes.com](mailto:sales@smc-diodes.com) •

**Marking Diagram:**

**ZF = CESD5V0D5**
**Cautions:** Molding resin  
 Epoxy resin UL:94V-0

**Ordering Information**

Device	Package	Shipping
CESD Series	SOD-523 (Pb-Free)	8000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings @ $T_A=25^\circ\text{C}$  unless otherwise specified**

Parameter	Symbol	Value	Unit
ESD per IEC 61000-4-2 (Air)	$V_{ESD}$	$\pm 30$	kV
ESD per IEC 61000-4-2 (Contact)		$\pm 30$	
Total power dissipation on FR-5 board (Note 1)	$P_D$	150	mW
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Lead Solder Temperature - Maximum (10 Second Duration)	$T_L$	260	$^\circ\text{C}$
Operating Junction Temperature Range	$T_J$	-55 to + 150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 to + 150	$^\circ\text{C}$

Note: 1. FR-5= 1.0 × 0.75 × 0.62 in.

**Electrical Characteristics:** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$
C	Max. Capacitance @ $V_R=0$ and $f=1\text{MHz}$

Device*	Device Marking	$V_{RWM}$ (V)	$I_R(\mu\text{A})$ @ $V_{RWM}$	$V_{BR}$ (V) @ $I_T$ (Note 2)		$I_T$	$V_C$ @ $I_{pp}^*=5\text{A}$	$I_{pp}$ (A)*	$V_C(\text{V})$ @ Max $I_{pp}^*$	C(pF)
		Max.	Max.	Min.	Max.	mA	V	Max.	Max.	Typ.
CESD3V3D5	ZE	3.3	0.08	5.0	5.9	1.0	9.4	11.2	14.1	105
CESD5V0D5	ZF	5.0	0.08	6.2	7.3	1.0	11.6	9.4	18.6	80
CESD7V0D5	ZH	7.0	0.03	7.5	8.7	1.0	13.5	8.8	22.7	65
CESD12VD5	ZM	12	0.02	14.1	15.7	1.0	23	9.6	29	55

\*Other voltages available upon request.

2.  $V_{BR}$  is measured with a pulse test current  $I_T$  at an ambient temperature of  $25^\circ\text{C}$ .

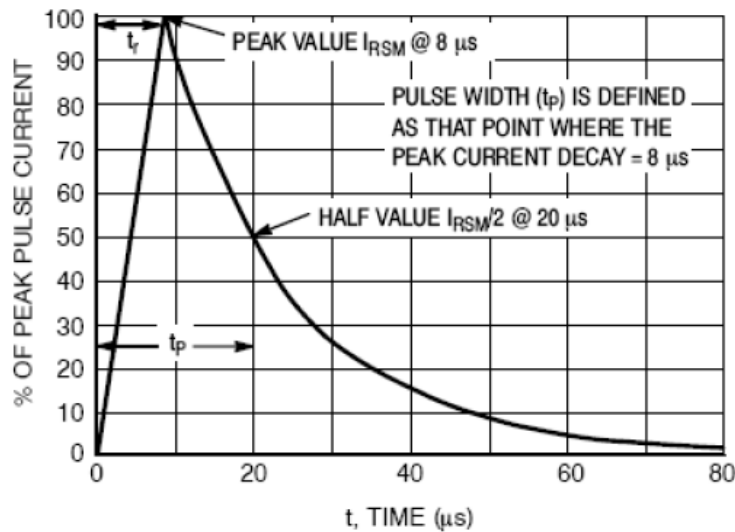


Figure 1. 8 x 20  $\mu\text{s}$  Pulse Waveform

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